# 74LVTN16244B

3.3 V 16-bit buffer/driver; 3-state
Rev. 3 — 14 June 2011

Product data sheet

#### 1. **General description**

The 74LVTN16244B is a high-performance BiCMOS product designed for  $V_{CC}$  operation at 3.3 V.

This device is a 16-bit buffer and line driver featuring non-inverting 3-state bus outputs. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer.

#### **Features and benefits** 2.

- 16-bit bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Power-up 3-state
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Latch-up protection
  - ◆ JESD78B Class II exceeds 500 mA
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V

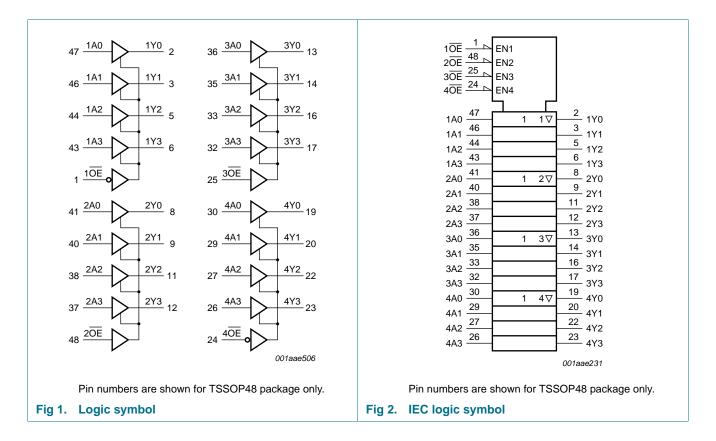
#### **Ordering information** 3.

Table 1. **Ordering information** 

Type number	Package									
	Temperature range	Name	Description	Version						
74LVTN16244BDGG	–40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1						
74LVTN16244BBX	–40 °C to +85 °C	HXQFN60U	plastic thermal enhanced extremely thin quad flat package; no leads; 60 terminals; UTLP based; body $4\times6\times0.5~\text{mm}$	SOT1134-1						

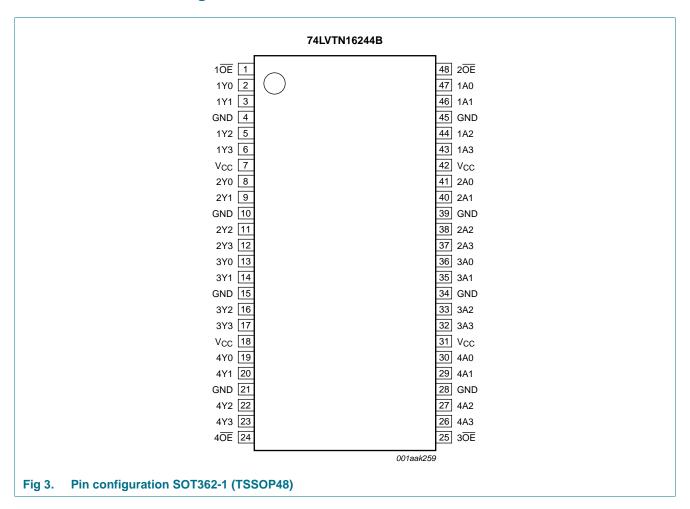


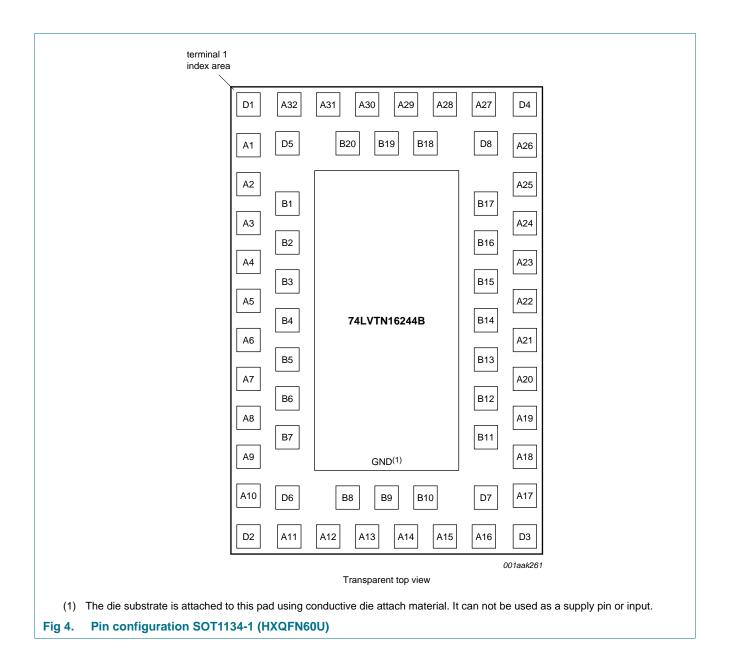
## 4. Functional diagram



## 5. Pinning information

### 5.1 Pinning





## 5.2 Pin description

Table 2. Pin description

Symbol	Pin		Description
	SOT362-1	SOT1134-1	
1 <u>OE</u> , 2 <u>OE</u> , 3OE, 4OE	1, 48, 25, 24	A30, A29, A14, A13	output enable input (active LOW)
1Y0 to 1Y3	2, 3, 5, 6	B20, A31, D5, D1	data output
2Y0 to 2Y3	8, 9, 11, 12	A2, B2, B3, A5	data output
3Y0 to 3Y3	13, 14, 16, 17	A6, B5, B6, A9	data output
4Y0 to 4Y3	19, 20, 22, 23	D2, D6, A12, B8	data output

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 Table 2.
 Pin description ...continued

Symbol	Pin		Description		
	SOT362-1	SOT1134-1	_		
GND	4, 10, 15, 21, 28, 34, 39, 45	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)		
V <sub>CC</sub>	7, 18, 31, 42	A1, A10, A17, A26	supply voltage		
1A0 to 1A3	47, 46, 44, 43	B18, A28, D8, D4	data input		
2A0 to 2A3	41, 40, 38, 37	A25, B16, B15, A22	data input		
3A0 to 3A3	36, 35, 33, 32	A21, B13, B12, A18	data input		
4A0 to 4A3 30, 29, 27, 26		D3, D7, A15, B10	data input		
n.c.	-	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected		

## 6. Functional description

Table 3. Function table [1]

Control	Input	Output
nOE	nAn	nYn
L	L	L
L	Н	Н
Н	X	Z

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
V <sub>I</sub>	input voltage		<u>[1]</u> –0.5	+7.0	V
V <sub>O</sub>	output voltage	output in OFF-state or HIGH-state	[ <u>1]</u> –0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
I <sub>O</sub>	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-64	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		[2] _	150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +85  ^{\circ}\text{C};$			
		TSSOP48 package	[3] _	500	mW
		HXQFN60U package	<u>[4]</u> _	1000	mW

<sup>[1]</sup> The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

# 8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		2.7	-	3.6	V
$V_{I}$	input voltage		0	-	5.5	V
$V_{IH}$	HIGH-level input voltage		2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage		-	-	0.8	V
I <sub>OH</sub>	HIGH-level output current		-32	-	-	mA
I <sub>OL</sub>	LOW-level output current	none	-	-	32	mA
		current duty cycle $\leq 50$ %; $f_i \geq 1 \text{ kHz}$	-	-	64	mA
T <sub>amb</sub>	ambient temperature	in free-air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

<sup>[2]</sup> The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

<sup>[3]</sup> Above 60 °C the value of Ptot derates linearly with 5.5 mW/K.

<sup>[4]</sup> Above 70 °C the value of  $P_{tot}$  derates linearly with 1.8 mW/K.

### 9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -	40 °C to +85 °C[1]					
$V_{IK}$	input clamping voltage	$V_{CC} = 2.7 \text{ V}; I_{IK} = -18 \text{ mA}$	-1.2	-0.85	-	V
V <sub>OH</sub>	HIGH-level output voltage	$I_{OH}$ = $-100 \mu A$ ; $V_{CC}$ = 2.7 V to 3.6 V	V <sub>CC</sub> - 0.2	$V_{CC}$	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.4	2.5	-	V
		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	2.3	-	V
$V_{OL}$	LOW-level output voltage	V <sub>CC</sub> = 2.7 V				
		I <sub>OL</sub> = 100 μA	-	0.07	0.2	V
		I <sub>OL</sub> = 24 mA	-	0.3	0.5	V
		V <sub>CC</sub> = 3.0 V				
		I <sub>OL</sub> = 16 mA	-	0.25	0.4	V
		I <sub>OL</sub> = 32 mA	-	0.3	0.5	V
		I <sub>OL</sub> = 64 mA	-	0.4	0.55	V
I <sub>I</sub>	input leakage current	all input pins; $V_{CC} = 0 \text{ V or } 3.6 \text{ V}; V_I = 5.5 \text{ V}$	-	0.1	10	μΑ
		control pins; $V_{CC} = 3.6 \text{ V}$ ; $V_I = V_{CC} \text{ or GND}$	-	0.1	±1.0	μΑ
		data pins; unused pins at V <sub>CC</sub> or GND				
		$V_{I} = V_{CC}; V_{CC} = 3.6 \text{ V}$	-	0.1	1	μΑ
		V <sub>I</sub> = 0 V; V <sub>CC</sub> = 3.6 V	-5	-0.1	-	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{CC} = 0 \text{ V}$ ; $V_I \text{ or } V_O = 0 \text{ V to } 4.5 \text{ V}$	-	0.1	±100	μΑ
I <sub>LO</sub>	output leakage current	output in HIGH-state when $V_O > V_{CC}$ ; $V_O = 5.5 \text{ V}$ ; $V_{CC} = 3.0 \text{ V}$	-	50	125	μΑ
I <sub>O(pu/pd)</sub>	power-up/power-down output current	$V_{CC} \le \underline{1.2} \text{ V; } V_O = 0.5 \text{ V to } V_{CC}; V_I = \text{GND or } V_{CC}; n\overline{\text{OE}} = \text{don't care}$	[2] -	1	±100	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_{CC} = 3.6 \text{ V}; V_I = V_{IH} \text{ or } V_{IL}$				
		output HIGH: V <sub>O</sub> = 3.0 V	-	0.5	5	μА
		output LOW: V <sub>O</sub> = 0.5 V	-5	+0.5	-	μА
I <sub>CC</sub>	supply current	$V_{CC} = 3.6 \text{ V}$ ; $V_I = \text{GND or } V_{CC}$ ; $I_O = 0 \text{ A}$				
		output HIGH	-	0.07	0.12	mA
		output LOW	-	4.0	6.0	mA
		outputs disabled	[3] _	0.07	0.12	mA
Δl <sub>CC</sub>	additional supply current	per input pin; $V_{CC}$ = 3.0 V to 3.6 V; one input at $V_{CC}$ – 0.6 V other inputs at $V_{CC}$ or GND	[4] -	0.1	0.2	mA
Cı	input capacitance	V <sub>I</sub> = 0 V or 3.0 V	-	3	-	pF
		outputs disabled; V <sub>O</sub> = 0 V or 3.0 V		9		pF

<sup>[1]</sup> Typical values are measured at  $V_{CC}$  = 3.3 V and at  $T_{amb}$  = 25 °C.

<sup>[2]</sup> This parameter is valid for any  $V_{CC}$  between 0 V and 1.2 V with a transition time of up to 10 ms. From  $V_{CC}$  = 1.2 V to  $V_{CC}$  = 3.3 V  $\pm$  0.3 V a transition time of 100  $\mu$ s is permitted. This parameter is valid for  $T_{amb}$  = 25 °C only.

<sup>[3]</sup>  $I_{CC}$  is measured with outputs pulled to  $V_{CC}$  or GND.

<sup>[4]</sup> This is the increase in supply current for each input at the specified voltage level other than  $V_{CC}$  or GND.

## 10. Dynamic characteristics

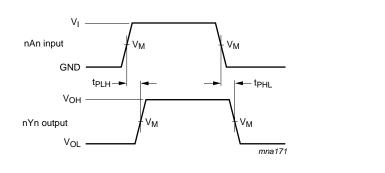
Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$T_{amb} = -40$	°C to +85 °C[1]					
t <sub>PLH</sub>	LOW to HIGH	nAn to nYn; see Figure 5				
	propagation delay	V <sub>CC</sub> = 2.7 V	-	-	4.0	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.5	1.8	3.2	ns
t <sub>PHL</sub>	HIGH to LOW	nAn to nYn; see Figure 5				
	propagation delay	V <sub>CC</sub> = 2.7 V	-	-	4.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.5	1.7	3.2	ns
t <sub>PZH</sub>	OFF-state to HIGH	nOE to nYn; see Figure 6				
	propagation delay	$V_{CC} = 2.7 \text{ V}$	-	-	5.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.3	4.0	ns
t <sub>PZL</sub>	OFF-state to LOW	nOE to nYn; see Figure 6				
	propagation delay	$V_{CC} = 2.7 \text{ V}$	-	-	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.1	4.0	ns
t <sub>PHZ</sub>	HIGH to OFF-state	nOE to nYn; see Figure 6				
	propagation delay	$V_{CC} = 2.7 \text{ V}$	-	-	5.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	3.2	4.5	ns
t <sub>PLZ</sub>	LOW to OFF-state	nOE to nYn; see Figure 6				
	propagation delay	$V_{CC} = 2.7 \text{ V}$	-	-	4.4	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	2.9	4.0	ns

<sup>[1]</sup> Typical values are measured at  $V_{CC}$  = 3.3 V and  $T_{amb}$  = 25 °C.

### 11. Waveforms



Measurements points are given in Table 8.

 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (nAn) to output (nYn)

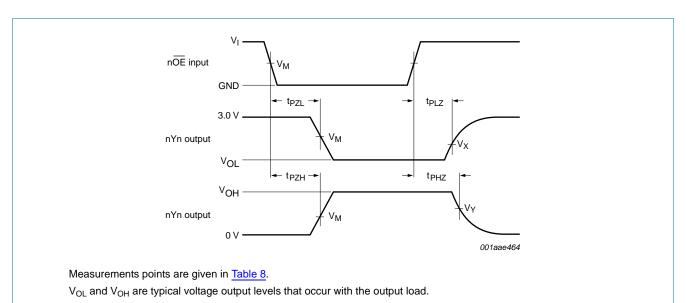
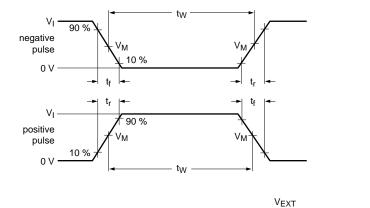
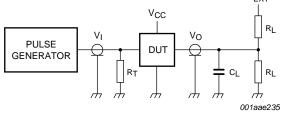


Fig 6. 3-state output enable and disable times

Table 8. Measurement points

Input	Output	utput							
$V_{M}$	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>						
1.5 V	1.5 V	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> – 0.3 V						





Test data is given in Table 9.

Definitions test circuit:

 $R_L$  = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $V_{\text{EXT}}$  = External voltage for measuring switching times.

Fig 7. Load circuit for measuring switching times

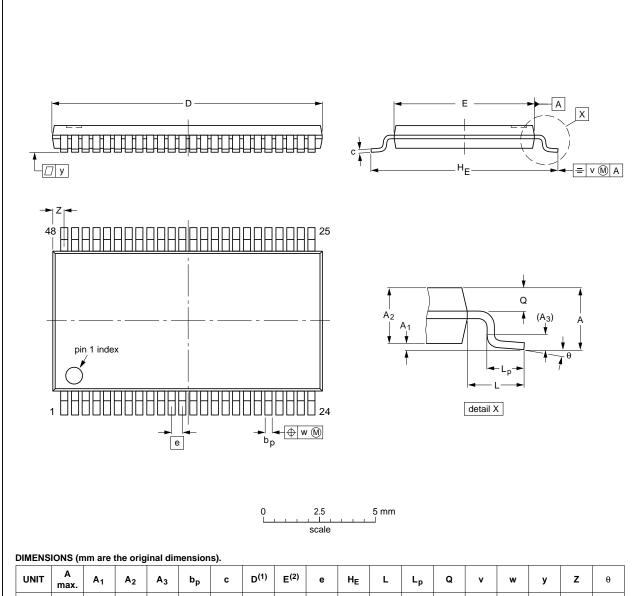
Table 9. Test data

Input				Load		V <sub>EXT</sub>			
$V_{I}$	f <sub>i</sub>	t <sub>W</sub>	t <sub>r</sub> , t <sub>f</sub>	C <sub>L</sub>	$R_L$	t <sub>PHZ</sub> , t <sub>PZH</sub>	$t_{PLZ}$ , $t_{PZL}$	t <sub>PLH</sub> , t <sub>PHL</sub>	
2.7 V	≤ 10 MHz	500 ns	≤ 2.5 ns	50 pF	$500 \Omega$	GND	6 V	open	

## 12. Package outline

TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm

SOT362-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	z	θ	
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	12.6 12.4	6.2 6.0	0.5	8.3 7.9	1	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.8 0.4	8° 0°	

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT362-1		MO-153				<del>99-12-27</del> 03-02-19
						0

Fig 8. Package outline SOT362-1 (TSSOP48)

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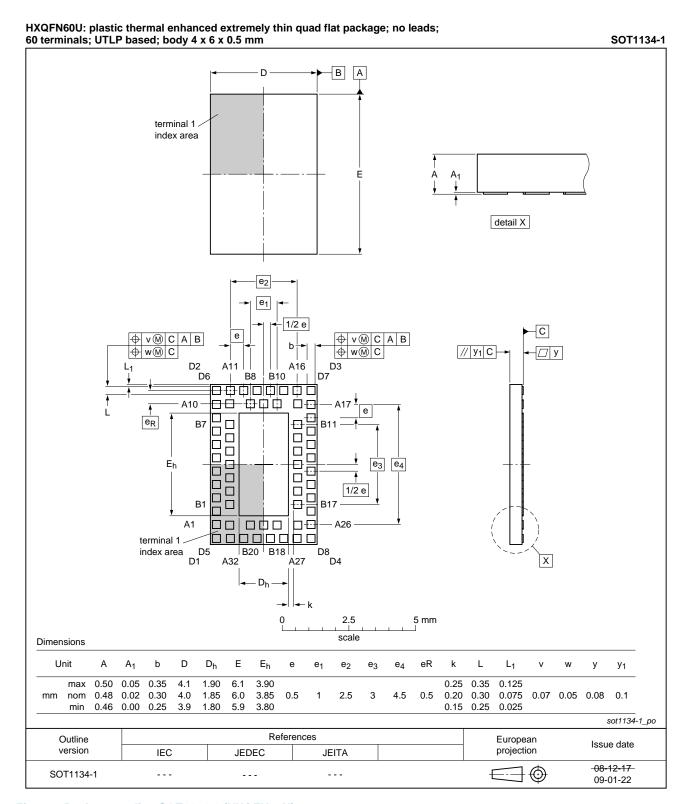


Fig 9. Package outline SOT1134-1 (HXQFN60U)

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## 13. Abbreviations

### Table 10. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 14. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVTN16244B v.3	20110614	Product data sheet	-	74LVTN16244B v.2
Modifications:	• 74LVTN162	44BBQ changed to 74LVT	N16244BBX for HXQFN	60U (SOT1134-1) package.
74LVTN16244B v.2	20100323	Product data sheet	-	74LVTN16244B v.1
Modifications:	<ul> <li>74LVTN162 package.</li> </ul>	44BBQ changed from HUC	QFN60U (SOT1025-1) to	HXQFN60U (SOT1134-1)
74LVTN16244B v.1	20090713	Product data sheet	-	-

## 15. Legal information

#### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# 74LVTN16244B

3.3 V 16-bit buffer/driver; 3-state

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